

SCHOTTKY DIE SPECIFICATION

TYPE: MBR2100

General Description: 100 V 2 A (Low Ir)

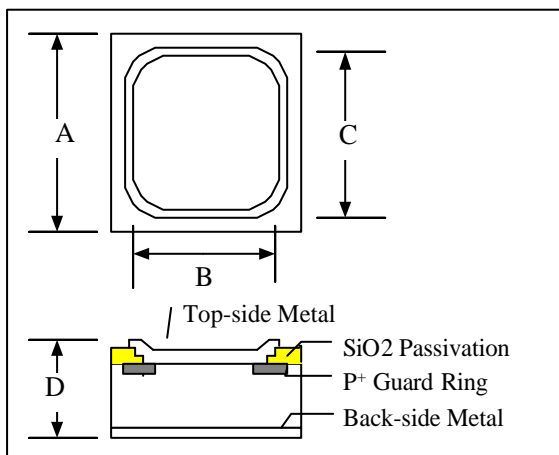
Single Anode

| ELECTRICAL CHARACTERISTICS | SYM | Spec. Limit | Die Sort | UNIT |
|---|--------|-------------|----------|------|
| DC Blocking Voltage: Ir=1mA(for wafer form) | VRRM | 100 | 105 | Volt |
| Ir=0.5mA (for dice form) | | | | |
| Average Rectified Forward Current | IFAV | 2 | | Amp |
| Maximum Instantaneous Forward Voltage | | | | |
| @ 1 Amperes, Ta=25°C | VF MAX | 0.74 | 0.73 | Volt |
| @ 2 Amperes, 25°C | | 0.82 | 0.81 | |
| Maximum Instantaneous Reverse Voltage | | | | |
| VR= 100 Volt, Ta=25°C | IR MAX | 0.1 | 0.09 | mA |
| | | | | |
| Maximum Junction Capacitance @ 0V, 1MHZ | Cj MAX | | | pF |
| MAXIMUM RATINGS | | | | |
| Nonrepetitive Peak Surge Current | IFSM | 50 | | Amp |
| Operating Junction Temperature | Tj | -65 to +125 | | °C |
| Storage Temperatures | TSTG | -65 to +125 | | °C |

Specification apply to die only. Actual performance may degrade when assembled.

MEMT does not guarantee device performance after assembly.

Data sheet information is subjected to change without notice.

DICE OUTLINE DRAWING


| DIM | ITEM | um ² | Mil ² |
|-----|--------------------|-----------------|------------------|
| A | Die Size | 1245 | 49.01 |
| B | Top Metal Pad Size | 1025 | 40.3 |
| C | Passivation Seal | 1203 | 47.3 |
| D | Thickness (Min) | 254 | 10 |
| | Thickness (Max) | 305 | 12 |

PS:

(1)Cutting street width is around 80um(3.14mil).

(2)Both of top-side and back-side metals are Ti/Ni/Ag.